

Products > RF ICs/Discretes > RF ICs > GaAs Amplifiers, Mixers, Switches > MGA-83563

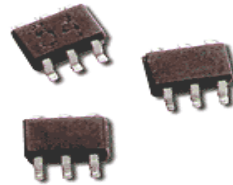
MGA-83563

3V PA/Driver, 22dBm PSAT, 0.5-6GHz, SOT363(SC-70)

Description



Lifecycle status: **Active**



Features

The MGA-83 is a 3V part with 20dBm P1dB. It is housed in the miniature SOT-363 package and designed for 3V driver amplifier applications. Bias: 3V, 142mA; Gain = 22dB; P1dB = 19dBm; IP3i = 7dB; PAE = 41% all at 2.4GHz.

MGA-83563

+22 dBm P_{SAT} 3V Power Amplifier for 0.5–6 GHz Applications



Data Sheet

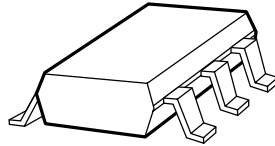
Description

Avago's MGA-83563 is an easy-to-use GaAs RFIC amplifier that offers excellent power output and efficiency. This part is targeted for 3V applications where constant-envelope modulation is used. The output of the amplifier is matched internally to 50Ω . However, an external match can be added for maximum efficiency and power out ($PAE = 37\%$, $P_o = 22\text{ dBm}$). The input is easily matched to 50Ω .

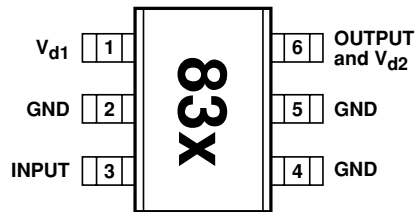
Due to the high power output of this device, it is recommended for use under a specific set of operating conditions. The thermal sections of the Applications Information explain this in detail.

The circuit uses state-of-the-art PHEMT technology with proven reliability. On-chip bias circuitry allows operation from single supply voltage.

Surface Mount Package SOT-363 (SC-70)

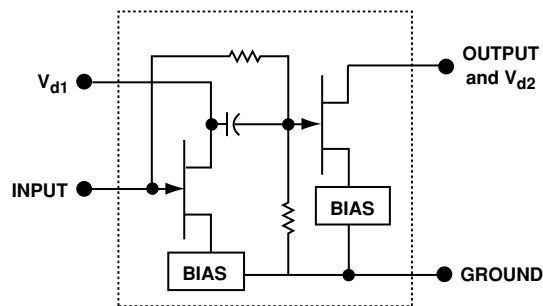


Pin Connections and Package Marking



Note:
Package marking provides orientation and identification; "x" is date code.

Equivalent Circuit (Simplified)



Features

- Lead-free Option Available
- +22 dBm P_{SAT} at 2.4 GHz, 3.0 V
- +23 dBm P_{SAT} at 2.4 GHz, 3.6 V
- 22 dB Small Signal Gain at 2.4 GHz
- Wide Frequency Range 0.5 to 6 GHz
- Single 3V Supply
- 37% Power Added Efficiency
- Ultra Miniature Package

Applications

- Amplifier for Driver and Output Applications



Attention:
Observe precautions for handling electrostatic sensitive devices.

ESD Machine Model (Class A)

ESD Human Body Model (Class 0)

Refer to Avago Application Note A004R: Electrostatic Discharge Damage and Control.

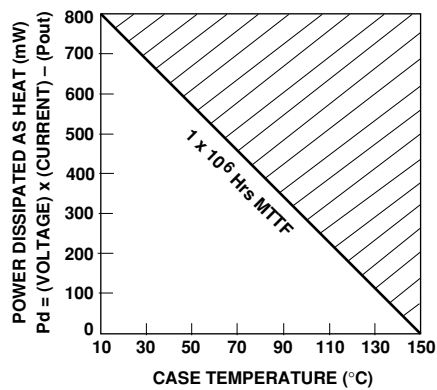
MGA-83563 Absolute Maximum Ratings

Symbol	Parameter	Units	Absolute Maximum ^[1]
V	Maximum DC Supply Voltage	V	4
P _{in}	CW RF Input Power	dBm	+13
T _{ch}	Channel Temperature	°C	165
T _{STG}	Storage Temperature	°C	-65 to 150

Thermal Resistance^[2]:
 $\theta_{ch\ to\ c} = 175^{\circ}\text{C}/\text{W}$

Notes:

1. Operation of this device above any one of these limits may cause permanent damage.
2. T_C = 25°C (T_C is defined to be the temperature at the package pins where contact is made to the circuit board).



Temperature/Power Derating Curve.

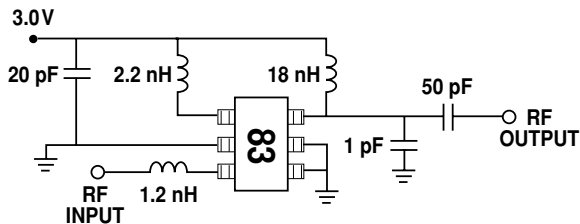
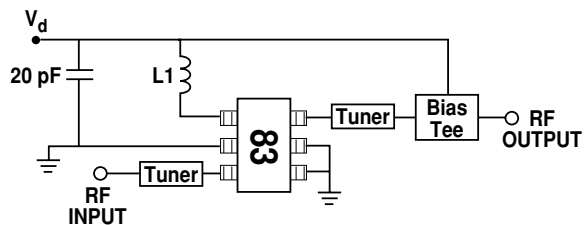


Figure 1. MGA-83563 Final Production Test Circuit.



Circuit A: L1 = 2.2 nH for 0.1 to 3 GHz
 Circuit B: L1 = 0 nH (capacitor as close as possible) for 3 to 6 GHz

Figure 2. MGA-83563 Test Circuit for Characterization.

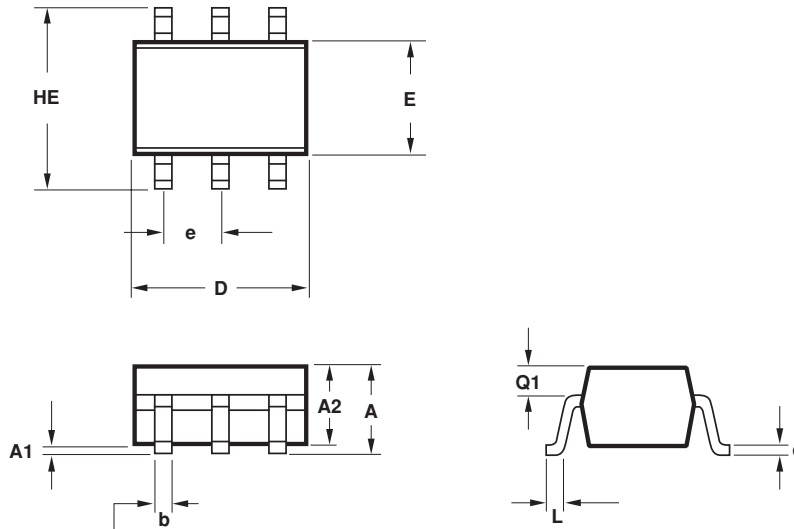
MGA-83563 Electrical Specifications, $V_d = 3\text{ V}$, $T_C = 25^\circ\text{C}$, using test circuit of Figure 2, unless noted.

Symbol	Parameters and Test Conditions	Units	Min.	Typ.	Max.	Std. Dev. [4]
P_{SAT}	Saturated Output Power ^[3] f = 2.4 GHz	dBm	20.5	22.4		0.75
PAE	Power Added Efficiency ^[3] f = 2.4 GHz	%	25	37		2.5
I_d	Device Current ^[3,5]	mA		152	200	12.4
Gain	Small Signal Gain f = 0.9 GHz f = 1.5 GHz f = 2.0 GHz f = 2.4 GHz f = 4.0 GHz f = 5.0 GHz f = 6.0 GHz	dB		20 22 23 22 22 19 17		
P_{SAT}	Saturated Output Power f = 0.9 GHz f = 1.5 GHz f = 2.0 GHz f = 2.4 GHz f = 4.0 GHz f = 5.0 GHz f = 6.0 GHz	dBm		20.9 21.7 21.8 22 21.9 19.7 18.2		
PAE	Power Added Efficiency f = 0.9 GHz f = 1.5 GHz f = 2.0 GHz f = 2.4 GHz f = 4.0 GHz f = 5.0 GHz f = 6.0 GHz	%		41 41 40 37 32 18 14		
$P_{1\text{ dB}}$	Output Power at 1 dB Gain Compression ^[5] f = 0.9 GHz f = 1.5 GHz f = 2.0 GHz f = 2.4 GHz f = 4.0 GHz f = 5.0 GHz f = 6.0 GHz	dBm		19.1 19.7 19.7 19.2 18.1 16 15		
$VSWR_{in}$	Input VSWR into 50 Ω Circuit A f = 0.9 to 1.7 GHz Circuit B f = 1.8 to 3.0 GHz f = 3.0 to 6.0 GHz			3.5 2.6 2.3		
$VSWR_{out}$	Output VSWR into 50 Ω Circuit A f = 0.9 to 2.0 GHz f = 2.0 to 3.0 GHz Circuit B f = 3.0 to 4.0 GHz f = 4.0 to 6.0 GHz			1.4 2.5 3.5 4.5		
ISOL	Isolation f = 0.9 to 3.0 GHz f = 3.0 to 6.0 GHz	dB		-38 -30		
IP_3	Third Order Intercept Point f = 0.9 GHz to 6.0 GHz	dBm		29		

Notes:

- Measured using the final test circuit of Figure 1 with an input power of +4 dBm.
- Standard Deviation number is based on measurement of at least 500 parts from three non-consecutive wafer lots during the initial characterization of this product, and is intended to be used as an estimate for distribution of the typical specification.
- For linear operation, refer to thermal sections in the Applications section of this data sheet.

Package Dimensions Outline 63 (SOT-363/SC-70)



SYMBOL	DIMENSIONS (mm)	
	MIN.	MAX.
E	1.15	1.35
D	1.80	2.25
HE	1.80	2.40
A	0.80	1.10
A2	0.80	1.00
A1	0.00	0.10
Q1	0.10	0.40
e	0.650 BCS	
b	0.15	0.30
c	0.10	0.20
L	0.10	0.30

NOTES:

1. All dimensions are in mm.
2. Dimensions are inclusive of plating.
3. Dimensions are exclusive of mold flash & metal burr.
4. All specifications comply to EIAJ SC70.
5. Die is facing up for mold and facing down for trim/form, ie: reverse trim/form.
6. Package surface to be mirror finish.

Part Number Ordering Information

Part Number	No. of Devices	Container
MGA-83563-TR1	3000	7" Reel
MGA-83563-TR2	10000	13" Reel
MGA-83563-BLK	100	antistatic bag
MGA-83563-TR1G	3000	7" Reel
MGA-83563-TR2G	10000	13" Reel
MGA-83563-BLKG	100	antistatic bag

Note: For lead-free option, the part number will have the character "G" at the end.